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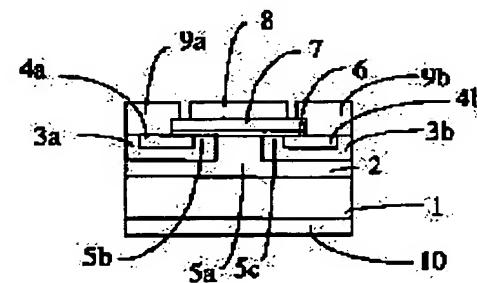
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(54) FORMATION METHOD FOR COMPOUND FILM AND MANUFACTURE OF SEMICONDUCTOR ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide the formation method of a compound film for forming a satisfactory compound film, in a short time, while turning a boundary between a semiconductor and the compound film formed on it into a satisfactory state and the manufacturing method of a semiconductor element using it.

SOLUTION: This forming method of a compound film is provided with a process for exposing the surfaces of semiconductors 2, 3a, 3b, 4a and 4b to atmospheric gas for forming a compound composed by combining with the constituent elements which constitute the semiconductor and forming a compound thin film 6 on the surfaces of the semiconductors 2, 3a, 3b, 4a and 4b and a process for forming a compound film 7 through a vapor phase formation method on the compound thin film 6.



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